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(54) METHOD OF REMOVING HARMFUL GAS FOR SEMICONDUCTOR

(57)Abstract:

PURPOSE: To remove harmful gases for semiconductors virtually perfectly by absorbing the gases for semiconductors by using a rotary type fine foam generator and using an aqueous potassium permanganate soln. as absorbing liquid.

CONSTITUTION: Gases for semiconductors such as arsine, phosphine, and diborane are absorbed and removed by using an aqueous potassium permanganate as absorbing liquid and using a rotary type fine foam generator. For example, 3l aqueous potassium permanganate soln. of 2.0wt% is put into a "Rotary Atomizer Model TOPCA-L-2", and while a rotor is being rotated at 2,000W2,500rpm, an N₂ gas contg. 100W20,000ppm arsine is introduced therein at the rate of 2W10l/min. The arsine concn. at the outlet is ≤0.5ppm. The suitable concn. of the aqueous potassium permanganate is 0.2W5.0wt%.

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